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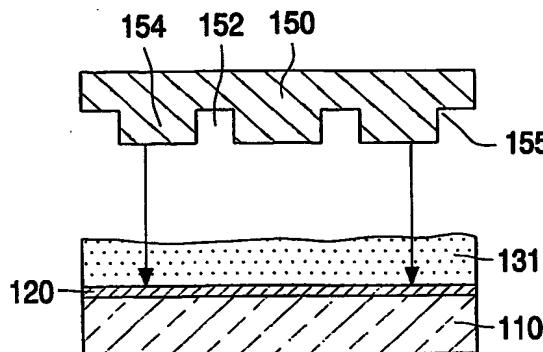
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(54) Title: **FIELD EMISSION DEVICE, AND METHOD OF MANUFACTURING SUCH A DEVICE**



(57) **Abstract:** A field emission device (100) is provided with a cathode electrode (120) and a gate electrode (140). Between these electrodes, a patterned dielectric layer (130) is provided. According to the invention, this dielectric layer (130) is manufactured from a liquid precursor material (131) which is patterned by means of a liquid embossing step, i.e. engaging a patterned stamp (150) with the liquid material (131). After removing the stamp (150), the liquid material is cured to form the patterned dielectric layer (130). Preferably, in a subsequent manufacturing step, the cathode electrode (120) or the gate electrode (140) is formed over the patterned dielectric layer (130) in a self-aligned way.

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